SIEMENS

Data sheet 3RF2120-3AA04



semiconductor relay, 1-phase 3RF2 width 22.5 mm, 20 A 48-460 V / 24 V DC ring cable terminal for mounting on available cooling surfaces

product brand name	SIRIUS
product designation	solid-state relay
design of the product	1-pole
product type designation	3RF21
manufacturer's article number	
_1 of the accessories that can be ordered	3RF2900-3PA88
_3 of the accessories that can be ordered	3RF2900-0EA18
_4 of the accessories that can be ordered	3RF2920-0GA16
product designation	
_1 of the accessories that can be ordered	terminal cover
_3 of the accessories that can be ordered	converter
_4 of the accessories that can be ordered	load monitoring
General technical data	
product function	zero-point switching
power loss [W] for rated value of the current	
 at AC in hot operating state 	28.6 W
 at AC in hot operating state per pole 	28.6 W
without load current share typical	0.4 W
insulation voltage rated value	600 V
surge voltage resistance of main circuit rated value	6 kV
protection class IP	IP00
protection class IP on the front according to IEC 60529	IP00
shock resistance according to IEC 60068-2-27	15g / 11 ms
vibration resistance according to IEC 60068-2-6	2g
reference code according to IEC 81346-2	Q
Substance Prohibitance (Date)	05/28/2009
SVHC substance name	Lead - 7439-92-1 Lead monoxide (lead oxide) - 1317-36-8
Weight	0.074 kg
Main circuit	
number of poles for main current circuit	1
number of NO contacts for main contacts	1
number of NC contacts for main contacts	0
type of voltage of the operating voltage	AC
operating voltage	
• at AC	
— at 50 Hz rated value	48 460 V
— at 60 Hz rated value	48 460 V
operating frequency rated value	50 60 Hz
relative symmetrical tolerance of the operating frequency	10 %

operating range relative to the operating voltage at AC	
● at 50 Hz	40 506 V
● at 60 Hz	40 506 V
operational current rated value maximum	20 A
operational current	
• at AC-51 rated value	20 A
 according to UL 508 rated value 	20 A
operational current minimum	100 mA
rate of voltage rise at the thyristor for main contacts	500 V/µs
maximum permissible	·
blocking voltage at the thyristor for main contacts maximum permissible	1 200 V
reverse current of the thyristor	10 mA
derating temperature	40 °C
surge current resistance rated value	200 A
I2t value maximum	200 A²-s
Control circuit/ Control	
type of voltage of the control supply voltage	DC
control supply voltage 1 at DC rated value maximum permissible	30 V
control supply voltage 1 at DC	15 24 V
control supply voltage	10 E 1 V
	45.1/
at DC initial value for signal <1> detection at DC full people value for signal <0> recognition	15 V
at DC full-scale value for signal<0> recognition	5 V
control current at minimum control supply voltage	40 4
• at DC	13 mA
control current at DC rated value	15 mA
ON-delay time	1 ms; additionally max. one half-wave
OFF-delay time	1 ms; additionally max. one half-wave
Auxiliary circuit	
type of switching contact	normally open contact (NO)
number of NC contacts for auxiliary contacts	0
number of NO contacts for auxiliary contacts	0
number of CO contacts for auxiliary contacts	0
Installation/ mounting/ dimensions	
fastening method side-by-side mounting	Yes
fastening method	screw fixing
design of the thread of the screw for securing the equipment	M4
tightening torque of fixing screw maximum	1.5 N·m
tightening torque [lbf·in] of fixing screw maximum	13 lbf·in
height	85 mm
width	22.5 mm
depth	48 mm
Connections/ Terminals	TO IIIII
	Voc
product component removable terminal for auxiliary and control circuit	Yes
type of electrical connection	
for main current circuit	Ring cable lug connection
for auxiliary and control circuit	ring terminal lug connection
type of connectable conductor cross-sections	
 for main contacts for JIS cable lug 	JIS C 2805 R 2-5, 5,5-5, 8-5, 14-5
for DIN cable lug for main contacts	DIN 46234 -5-2,5, -5-6, -5-10, -5-16, -5-25
type of connectable conductor cross-sections	
 for auxiliary and control contacts 	
— solid	1x (0.5 2.5 mm²), 2x (0.5 1 mm²)
 finely stranded with core end processing 	1x (0.5 2.5 mm²), 2x (0.5 1 mm²)
finely stranded without core end processing	1x (0.5 2.5 mm²), 2x (0.5 1 mm²)
for AWG cables for auxiliary and control contacts	1x (20 12)
tightening torque	(· -)
for main contacts with screw-type terminals	2 2.5 N·m
for auxiliary and control contacts with screw-type	
	0.5 0.6 N·m

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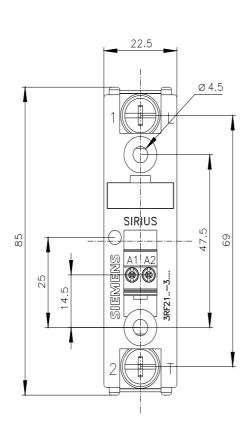
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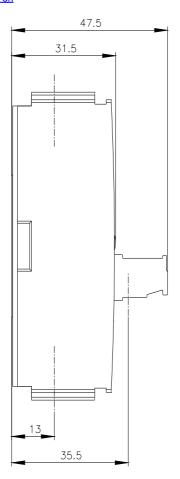
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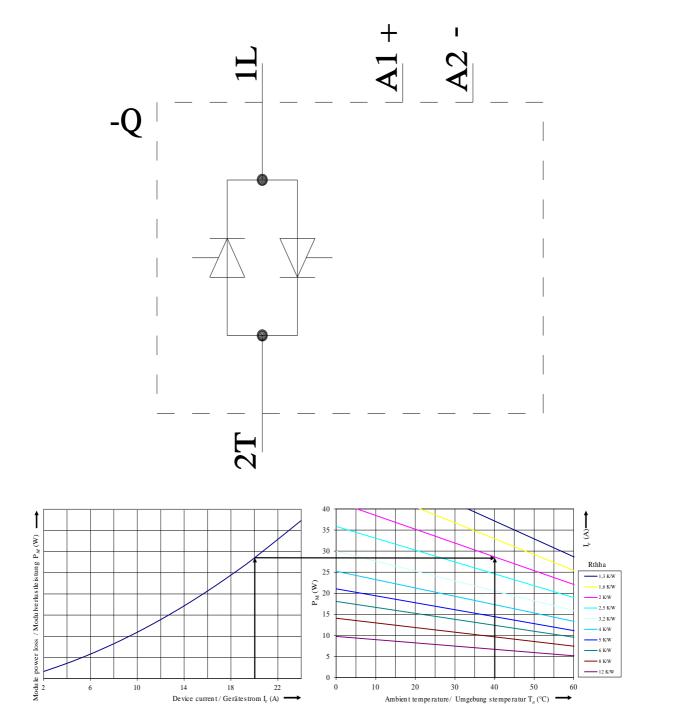
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